

N-CHANNEL SILICON POWER MOSFET

F- I SERIES

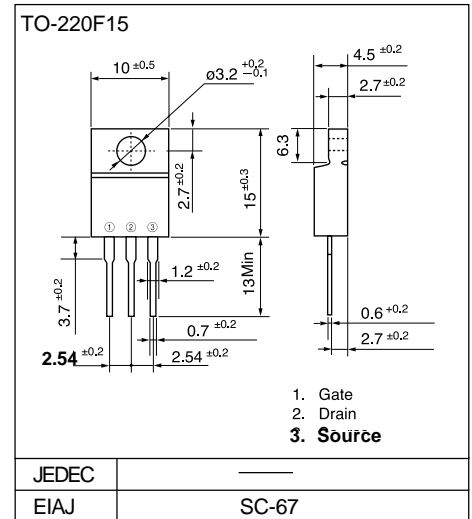
■ Features

- High current
- Low on-resistance
- No secondary breakdown
- Low driving power
- High voltage

■ Applications

- Switching regulators
- UPS
- DC-DC converters
- General purpose power amplifier

■ Outline Drawings

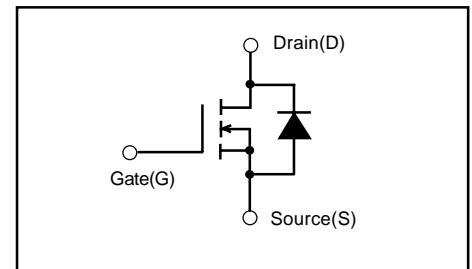


■ Maximum ratings and characteristics

● Absolute maximum ratings (T_c=25°C unless otherwise specified)

Item	Symbol	Rating	Unit
Drain-source voltage	V _{DS}	500	V
Continuous drain current	I _D	6	A
Pulsed drain current	I _{D(puls)}	24	A
Continuous reverse drain current	I _{DR}	6	A
Gate-source peak voltage	V _{GS}	±20	V
Max. power dissipation	P _D	40	W
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C

■ Equivalent circuit schematic



● Electrical characteristics (T_c =25°C unless otherwise specified)

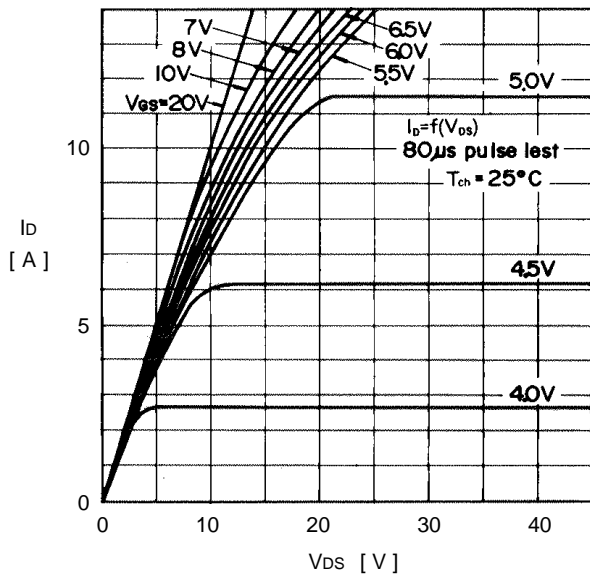
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =1mA V _{GS} =0V	500			V
Gate threshold voltage	V _{GS(th)}	I _D =10mA V _{DS} =V _{GS}	2.1	3.0	4.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =500V V _{GS} =0V	T _{ch} =25°C	10	500	μA
			T _{ch} =125°C	0.2	1.0	mA
Gate-source leakage current	I _{GSS}	V _{GS} =±20V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =3.5A V _{GS} =10V		1.0	1.2	Ω
Forward transconductance	g _{fs}	I _D =3.5A V _{DS} =25V	4.0	7.0		S
Input capacitance	C _{iss}	V _{DS} =25V		1200	1800	pF
Output capacitance	C _{oss}	V _{GS} =0V		120	180	
Reverse transfer capacitance	C _{rss}	f=1MHz		35	55	
Turn-on time t _{on} (t _{on} =t _{d(on)} +t _r)	t _{d(on)}	V _{CC} =30V R _G =50 Ω		25	40	ns
	t _r	I _D =2.7A		40	70	
Turn-off time t _{off} (t _{off} =t _{d(off)} +t _f)	t _{d(off)}	V _{GS} =10V		200	300	ns
	t _f			60	100	
Diode forward on-voltage	V _{SD}	I _F =2I _{DR} V _{GS} =0V T _{ch} =25°C		1.0	1.5	V
Reverse recovery time	t _{rr}	I _F =I _{DR} di/dt=100A/μs T _{ch} =25°C		300		ns

● Thermal characteristics

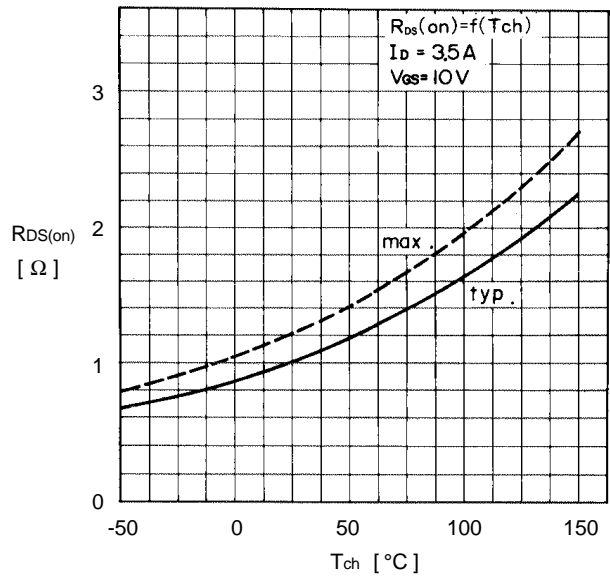
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-a)}	channel to ambient			62.5	°C/W
	R _{th(ch-c)}	channel to case			3.125	°C/W

Characteristics

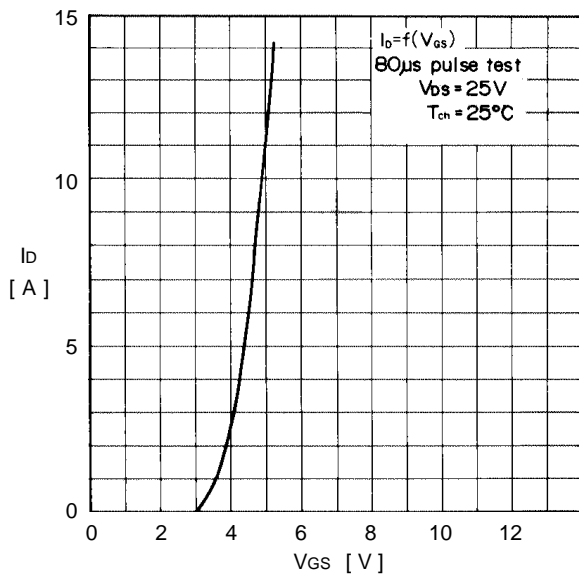
Typical output characteristics



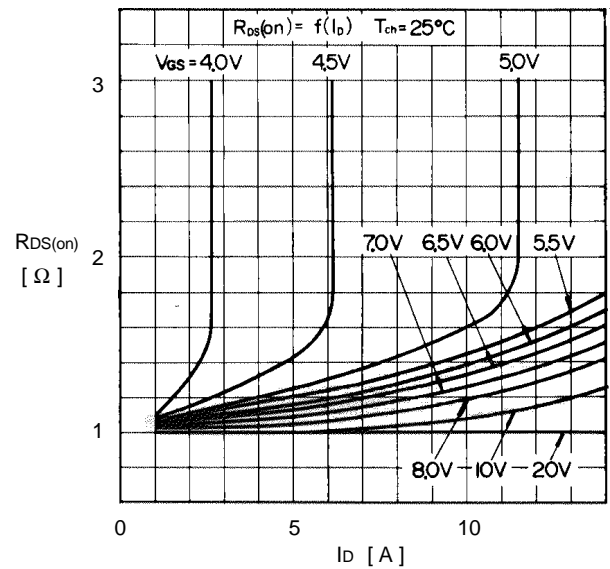
On state resistance vs. T_{ch}



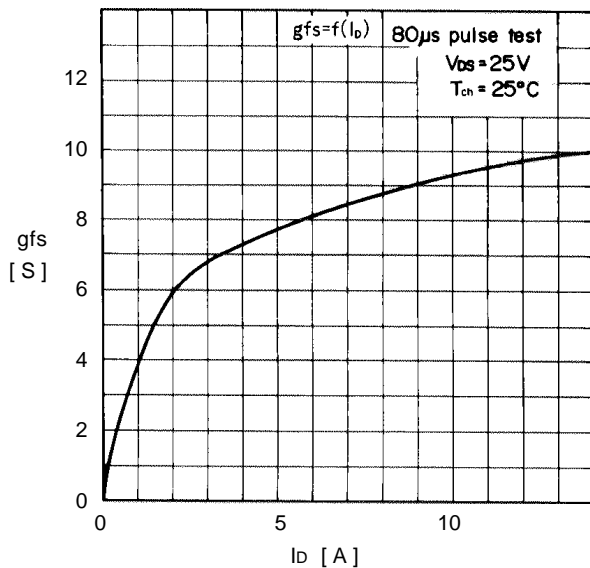
Typical transfer characteristics



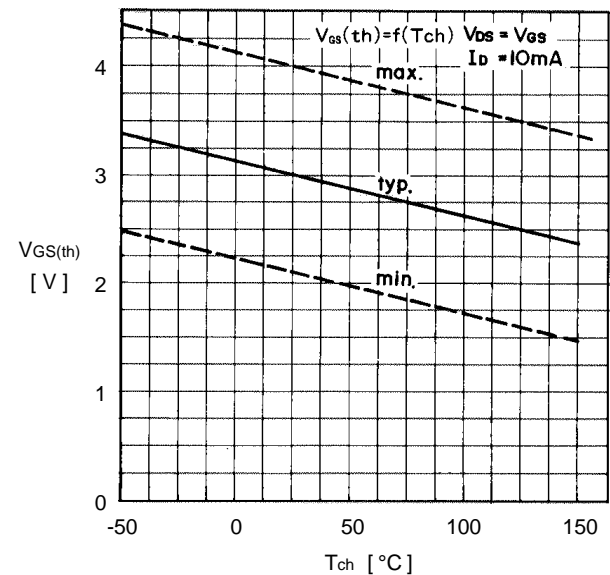
Typical Drain-Source on state resistance vs. I_D



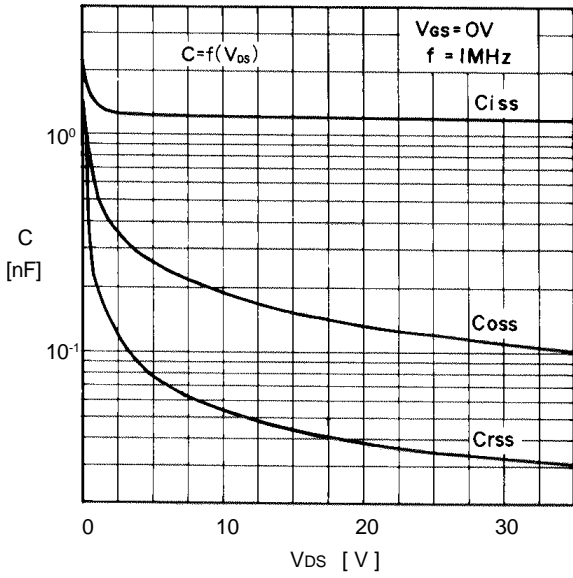
Typical forward transconductance vs. I_D



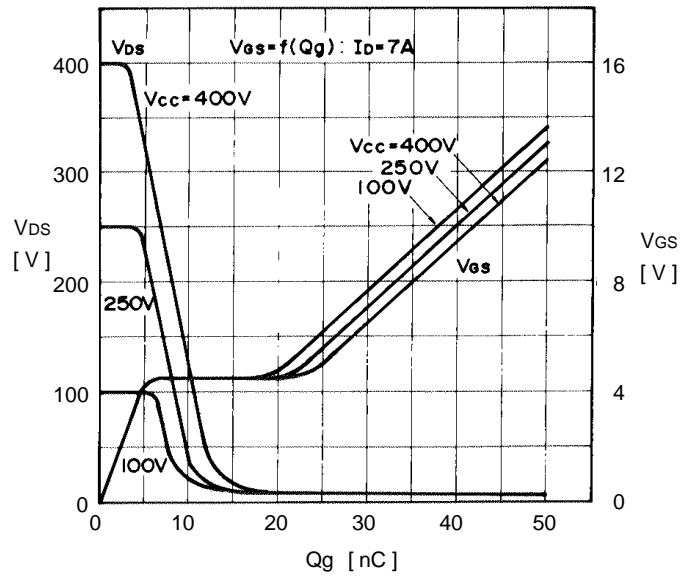
Gate threshold voltage vs. T_{ch}



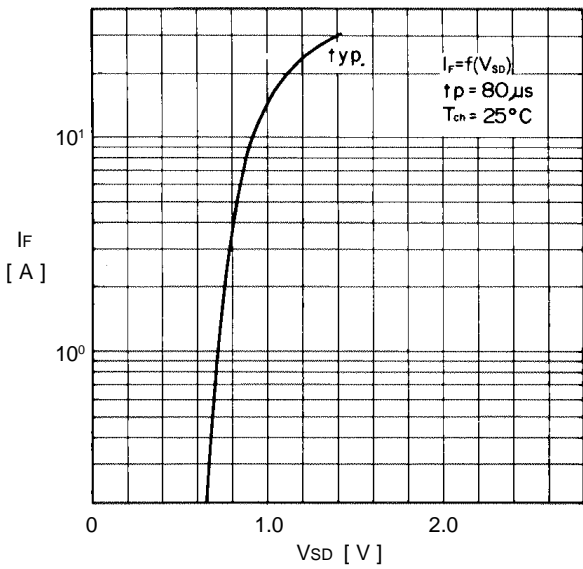
Typical capacitance vs. V_{DS}



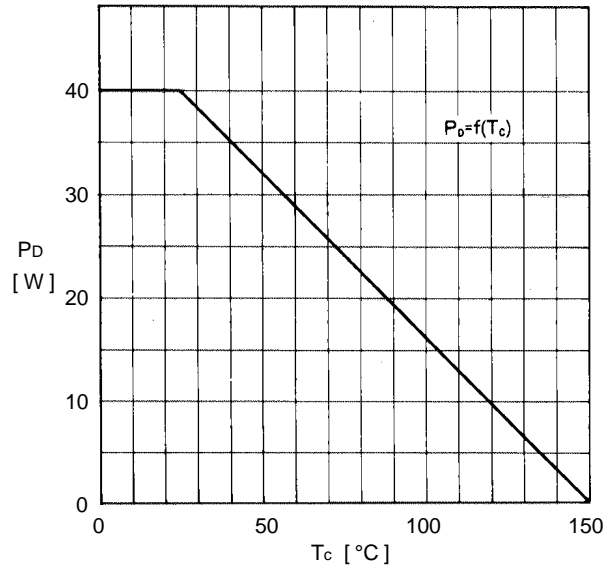
Typical input charge



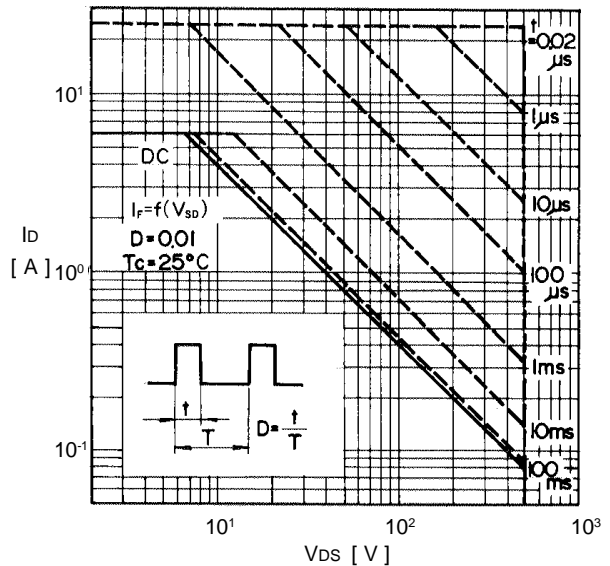
Forward characteristics of reverse diode



Allowable power dissipation vs. T_c



Safe operating area



Transient thermal impedance

